10563269 CLSTITLES.txt

Titles of most frequently occurring classifications of patents returned from a search of 10/563,269 on Jan 30, 2008

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20 257/E33.028 (0 OR, 20 XR)
     Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
     257/E33.001 .LIGHT EMITTING SEMICONDUCTOR DEVICES HAVING A POTENTIAL OR A SURFACE
BARRIER, PROCESSES OR APPARATUS PECULIAR TO THE MANUFACTURE OR TREATMENT OF SUCH
DEVICES, OR OF PARTS THEREOF
     257/E33.002 ... Device characterized by semiconductor body (EPO)
     257/E33.013 ... Material of active region (EPO)
     257/E33.023 ....Comprising only Group III-V compound (EPO)
     257/E33.026 .....Ternary or quaternary compound (e.g., AlGaAs) (EPO)
     257/E33.028 ......Including nitride (e.g., AlGaN) (EPO)
19 257/103
              (6 OR, 13 XR)
                ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
     Class 257
               INCOHERENT LIGHT EMITTER STRUCTURE
     257/79
     257/103
               ..With particular semiconductor material
11 257/96
             (4 OR, 7 XR)
     Class 257
               ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
     257/79
               .INCOHERENT LIGHT EMITTER STRUCTURE
     257/94
               ..With heterojunction
     257/96
               ...Plural heterojunctions in same device
 9 438/46
             (5 OR, 4 XR)
               SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
     Class 438
     438/22
               .MAKING DEVICE OR CIRCUIT EMISSIVE OF NONELECTRICAL SIGNAL
     438/46
               .. Compound semiconductor
 9 257/94
             (0 OR, 9 XR)
                ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
     Class 257
     257/79
               INCOHERENT LIGHT EMITTER STRUCTURE
     257/94
               ..With heterojunction
 8 372/45.01 (3 OR, 5 XR)
     Class 372 COHERENT LIGHT GENERATORS
     372/39
               .PARTICULAR ACTIVE MEDIA
     372/43.01 ...Semiconductor
     372/44.01 ...Injection
     372/45.01 ....Particular confinement laver
 8 257/76
             (1 OR, 7 XR)
     Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
               .SPECIFIED WIDE BAND GAP (1.5eV) SEMICONDUCTOR MATERIAL OTHER THAN GAASP
     257/76
or GaAlAs
 7 372/46.01 (4 OR, 3 XR)
                COHERENT LIGHT GENERATORS
     Class 372
     372/39
               .PARTICULAR ACTIVE MEDIA
     372/43.01 ...Semiconductor
     372/44.01
                ...Injection
     372/46.01
                ....Particular current control structure
 7 257/190
             (2 OR, 5 XR)
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10563269_CLSTITLES.txt

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/183 .HETEROJUNCTION DEVICE

257/190 ...With lattice constant mismatch (e.g., with buffer layer to accommodate mismatch)

6 257/E33.03 (0 OR, 6 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES) 257/E33.001 .LIGHT EMITTING SEMICONDUCTOR DEVICES HAVING A POTENTIAL OR A SURFACE BARRIER, PROCESSES OR APPARATUS PECULIAR TO THE MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF

257/E33.002 ... Device characterized by semiconductor body (EPO)

257/E33.013 ...Material of active region (EPO)

257/E33.023Comprising only Group III-V compound (EPO)

257/E33.029Characterized by doping material (EPO)

257/E33.03Nitride compound (EPO)

6 257/97 (0 OR, 6 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/79 .INCOHERENT LIGHT EMITTER STRUCTURE

257/94 .. With heterojunction

257/96 ...Plural heterojunctions in same device

257/97 More than two heterojunctions in same device